



MMIC SURFACE MOUNT

# Wideband Amplifier

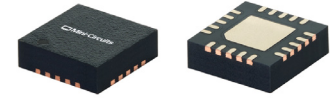
## AVA-183MP+

Mini-Circuits

50Ω 0.05 to 18 GHz High Dynamic Range Low Noise

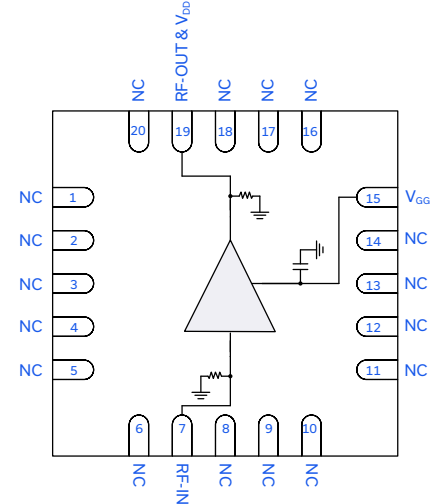
### THE BIG DEAL

- Ultra wideband, 0.05-18 GHz
- High Dynamic Range
  - P1dB, Typ. +24 dBm
  - Gain, Typ. 16 dB
  - Low Noise Figure, Typ. 1.8 dB
- High OIP3, Typ. +31 dBm
- 4x4mm 20-Lead QFN-Style Package



Generic photo used for illustration purposes only

### FUNCTIONAL DIAGRAM



### APPLICATIONS

- 5G MIMO and Back Haul Radio Systems
- Satellite Communications
- Test and Measurement Equipment
- Radar, EW, and ECM Defense Systems

### PRODUCT OVERVIEW

AVA-183MP+ is a GaAs pHEMT MMIC wideband distributed amplifier operating from 0.05 to 18 GHz. The amplifier provides 16.5 dB of Gain, +24 dBm P1dB, and +31 dBm OIP3, and 1.8 dB Noise Figure typical performance while operating from an +8V supply with 160mA current consumption. The AVA-183MP+ offers a leading combination of wide bandwidth, low noise figure, high linearity, and output power resulting in a 50Ω matched high dynamic range amplifier. The AVA-183MP+ performance characteristics are ideal for use in wideband Defense Systems and Test and Measurement Equipment. The amplifier is housed in an industry standard 4x4mm QFN-style package.

### KEY FEATURES

Features	Advantages
Wideband: 0.05 to 18 GHz • Gain, Typ. 16 dB	Ideal for use in wideband Electronic Warfare and Test and Measurement transmit signal chains.
High Dynamic Range • P1dB, Typ. +24 dBm • OIP3, Typ. +31 dBm • NF, Typ. 1.8 dB	Suitable as a driver amplifier for wideband power amplifier signal chains.
Good Input and Output Return Loss	Internally matched to 50Ω, this eliminates the need for external matching components making the device easy to integrate.
4x4mm 20-Lead QFN-style package	Small footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent thermal contact to the PCB.





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ELECTRICAL SPECIFICATIONS<sup>1</sup> AT +25°C, V<sub>DD</sub> = +8V, I<sub>DD</sub> = 160mA, UNLESS NOTED OTHERWISE

Parameter	Condition (GHz)	Min.	Typ.	Max.	Units
Frequency Range		0.05		18	GHz
Gain	0.05	20.0	20.6		dB
	5	15.7	16.2		
	10	15.9	16.5		
	15	15.5	16.3		
	18	15.2	16.3		
Input Return Loss	0.05		11.4		dB
	5		20.0		
	10		13.6		
	15		11.2		
	18		15.9		
Output Return Loss	0.05		14.3		dB
	5		20.0		
	10		20.0		
	15		20.0		
	18		19.3		
Isolation	0.05-18		43.0		dB
Output Power at 1 dB Compression (P1dB)	0.05		+25.8		dBm
	5		+24.2		
	10		+23.8		
	15		+24.4		
	18		+24.4		
Output Third-Order Intercept Point (P <sub>OUT</sub> = 0dBm/Tone)	0.05		+32.7		dBm
	5		+32.2		
	10		+31.1		
	15		+29.3		
	18		+27.4		
Noise Figure	0.05		7.0		dB
	5		1.5		
	10		1.8		
	15		2.8		
	18		3.6		
Device Operating Voltage (V <sub>DD</sub> )		+7.75	+8	+8.25	V
Device Operating Current (I <sub>DD</sub> ) <sup>2</sup>			160		mA
Gate Voltage (V <sub>GG</sub> ) <sup>3</sup>			-1.3		V
Gate Current (I <sub>GG</sub> )			-0.5		μA
Device Current Variation Vs. Temperature <sup>4</sup>			5.4		μA/°C
Device Current Variation Vs. Voltage <sup>5</sup>			0.208		mA/mV

1. Tested in Mini-Circuits Characterization Test/Evaluation Board TB-AVA-183MPC+. See Figure 2. De-embedded to the device reference plane.

2. Current at P<sub>IN</sub> = -25 dBm. Increases to 190 mA at P1dB.

3. Typical Gate Voltage for when I<sub>DD</sub> = 160 mA. V<sub>GG</sub> must be adjusted so that I<sub>DD</sub> = 160 mA.

4. ((Current at T<sub>max</sub>°C - Current at T<sub>min</sub>°C))/(T<sub>max</sub>°C - T<sub>min</sub>°C)

5. (Current at Nominal V +ΔV in mA) - (Current at Nominal V -ΔV in mA)/(2ΔV mV)

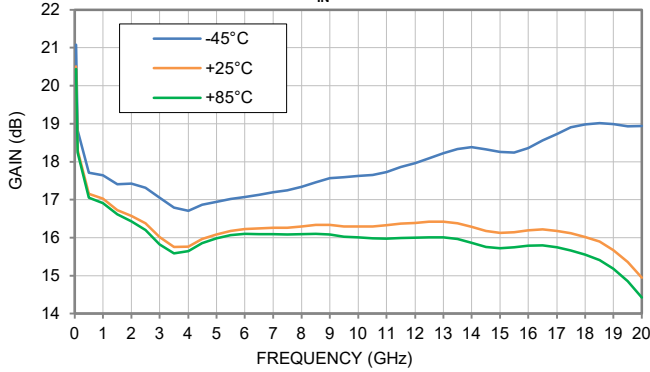




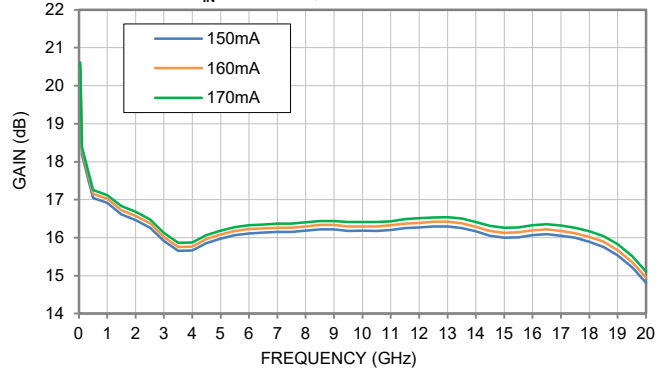
### TYPICAL PERFORMANCE GRAPHS

All data taken was at nominal conditions  $V_{DD} = +8V$  and  $I_{DD} = 160\text{ mA}$  unless noted otherwise. For over temperature data,  $I_{DD}$  is adjusted to 160 mA at each temperature specified. For over current data,  $V_{DD}$  is set to +8V and  $V_{GG}$  is adjusted until each specified current level is achieved.

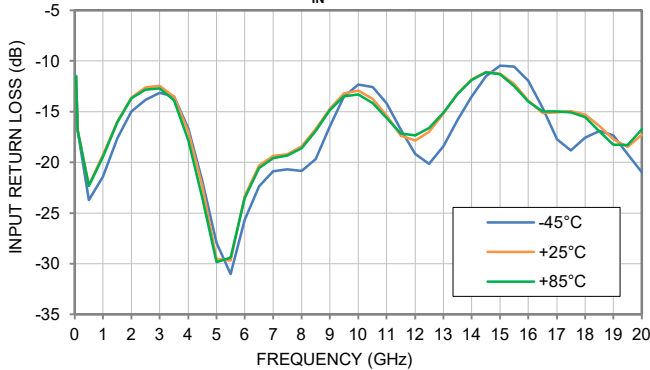
**GAIN vs. TEMPERATURE,**  
 $P_{IN} = -25\text{ dBm}$



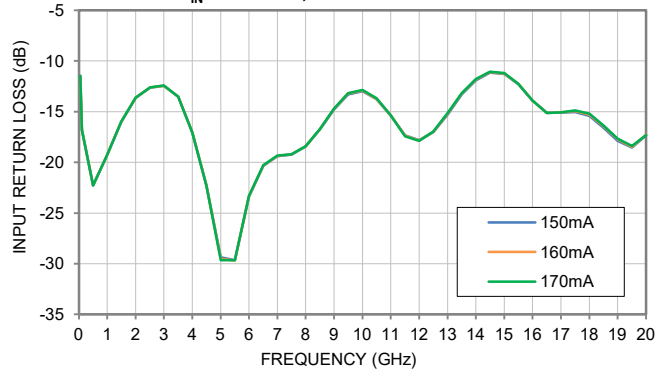
**GAIN vs. DEVICE CURRENT,**  
 $P_{IN} = -25\text{ dBm}$ , TEMPERATURE = +25°C



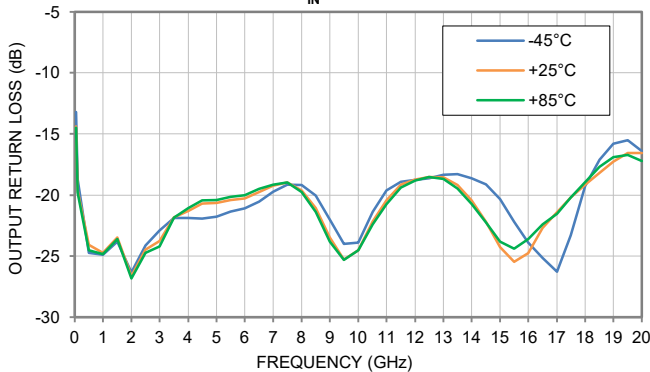
**INPUT RETURN LOSS vs. TEMPERATURE,**  
 $P_{IN} = -25\text{ dBm}$



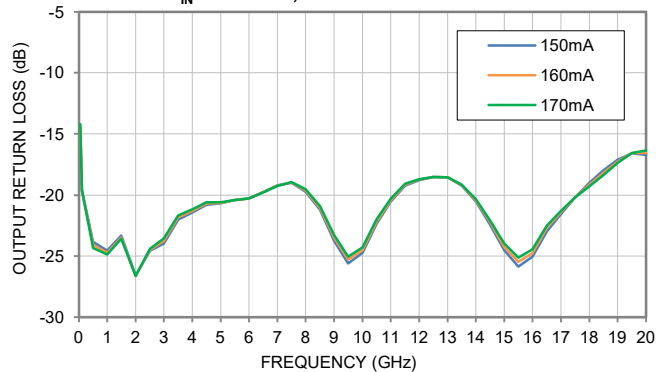
**INPUT RETURN LOSS vs. DEVICE CURRENT,**  
 $P_{IN} = -25\text{ dBm}$ , TEMPERATURE = +25°C



**OUTPUT RETURN LOSS vs. TEMPERATURE,**  
 $P_{IN} = -25\text{ dBm}$



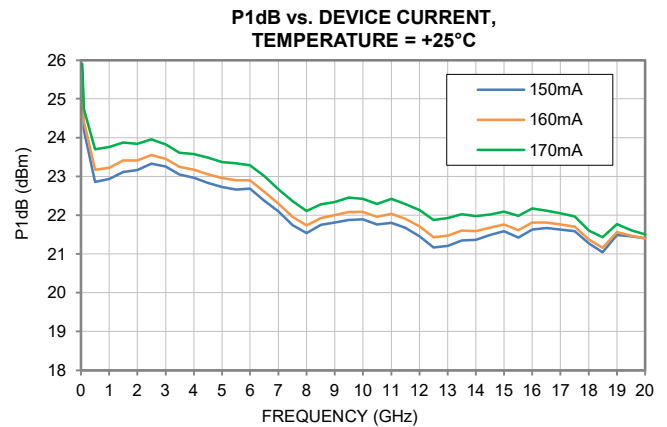
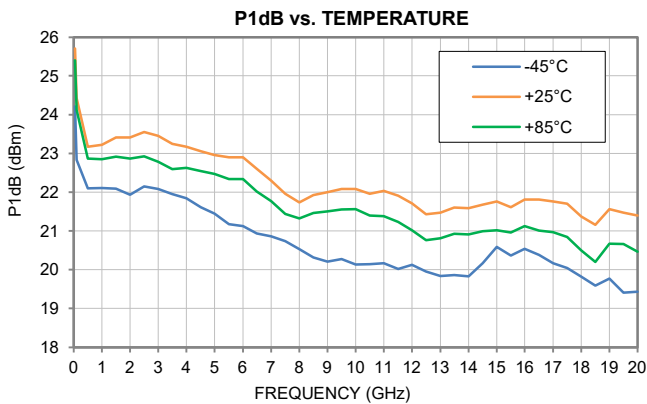
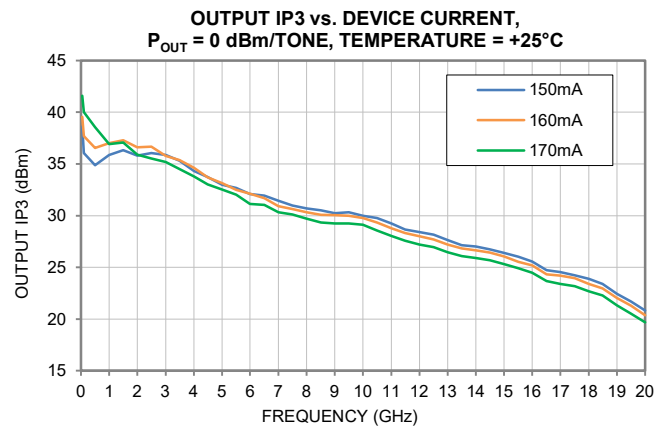
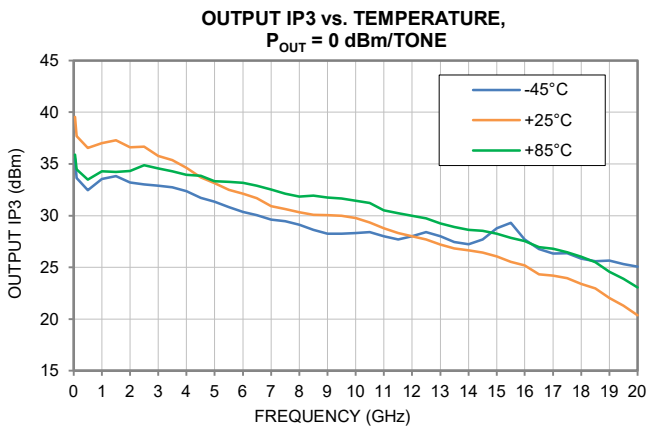
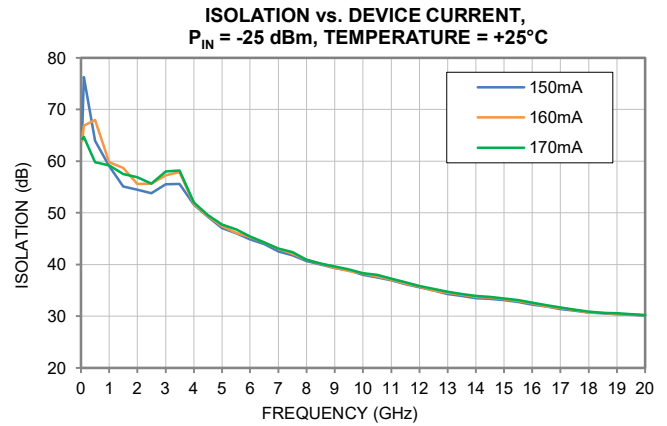
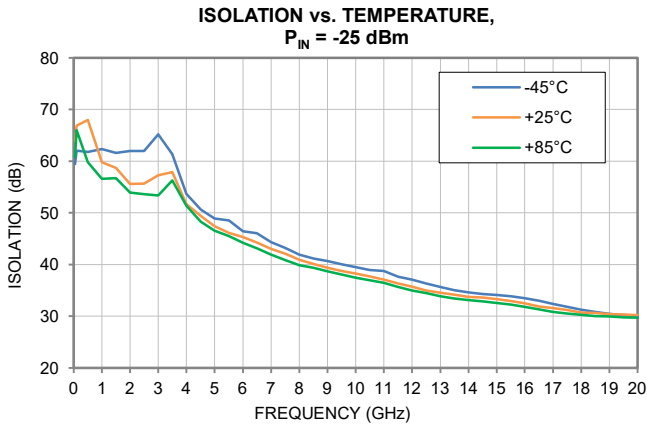
**OUTPUT RETURN LOSS vs. DEVICE CURRENT,**  
 $P_{IN} = -25\text{ dBm}$ , TEMPERATURE = +25°C





### TYPICAL PERFORMANCE GRAPHS

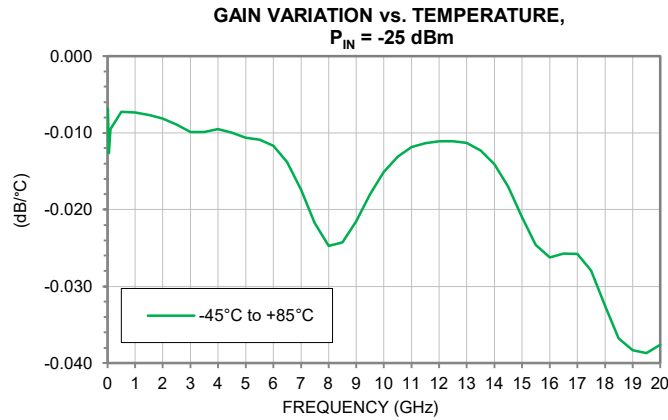
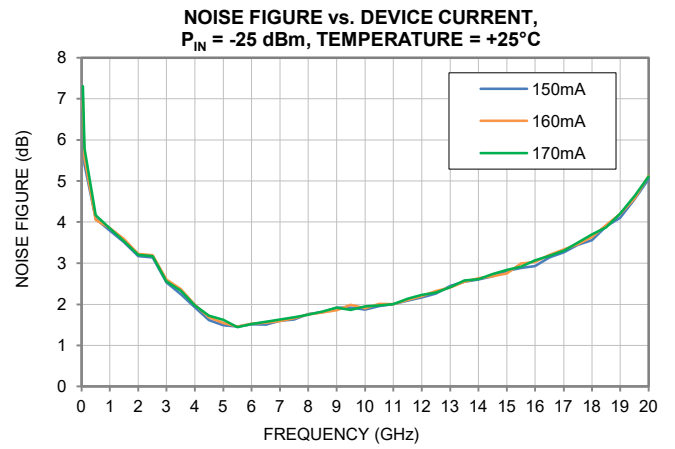
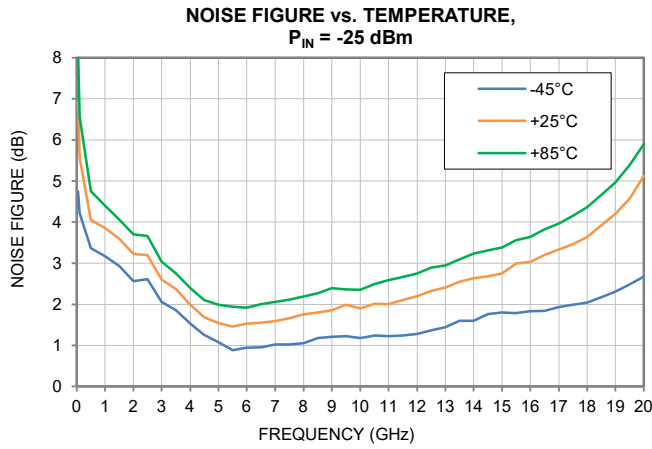
All data taken was at nominal conditions  $V_{DD} = +8V$  and  $I_{DD} = 160\text{ mA}$  unless noted otherwise. For over temperature data,  $I_{DD}$  is adjusted to 160 mA at each temperature specified. For over current data,  $V_{DD}$  is set to +8V and  $V_{GG}$  is adjusted until each specified current level is achieved.





### TYPICAL PERFORMANCE GRAPHS

All data taken was at nominal conditions  $V_{DD} = +8V$  and  $I_{DD} = 160\text{ mA}$  unless noted otherwise. For over temperature data,  $I_{DD}$  is adjusted to 160 mA at each temperature specified. For over current data,  $V_{DD}$  is set to +8V and  $V_{GG}$  is adjusted until each specified current level is achieved.





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### ABSOLUTE MAXIMUM RATINGS<sup>6</sup>

Parameter	Ratings
Operating Temperature	-45°C to +85°C
Storage Temperature	-65°C to +150°C
Total Power Dissipation	2.8W
Junction Temperature <sup>7</sup>	+175°C
Input Power (CW), $V_{DD} = +8V$ , $I_{DD} = 160mA$	+21 dBm (Continuous)
DC Voltage on RF-OUT & $V_{DD}$	+10V
DC Voltage on RF-IN	+10V
DC Voltage on $V_{GG}$	-0.5V to -2V
Current $I_{DD}$	350mA
Current $I_{GG}$	-1.5mA to 0mA

6. Permanent damage may occur if any of these limits are exceeded. Maximum ratings are not intended for continuous normal operation.

7. Peak temperature on top of Die.

### THERMAL RESISTANCE

Parameter	Ratings
Thermal Resistance ( $\Theta_{jc}$ ) <sup>8</sup>	17.3 °C/W

8.  $\Theta_{jc}$  = (Hot Spot Temperature on Die - Temperature at Ground Lead)/Dissipated Power

### ESD RATING

	Class	Voltage Range	Reference Standard
Human Body Model (HBM)	1B	500V to <1000V	ANSI/ESDA/JEDEC JS-001-2017
Charged Device Model (CDM)	C3	1000V	JESD22-C101F



ESD HANDLING PRECAUTION: This device is designed to be Class 1B for HBM. Static charges may easily produce potentials higher than this with improper handling and can discharge into DUT and damage it. As a preventive measure Industry standard ESD handling precautions should be used at all times to protect the device from ESD damage.

### MSL RATING

Moisture Sensitivity: MSL3 in accordance with IPC/JEDEC J-STD-020E/JEDEC J-STD-033C





### FUNCTIONAL DIAGRAM

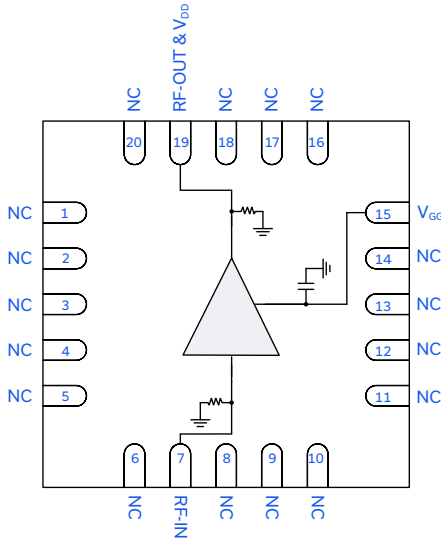


Figure 1. AVA-183MP+ Functional Diagram

### PAD DESCRIPTION

Function	Pad Number	Description
RF-IN	7	RF-IN Pad connects to RF-Input port. DUT includes an integrated shunt resistor for ESD protection.
RF-OUT & V <sub>DD</sub>	19	RF-OUT & V <sub>DD</sub> Pad connects to RF-Output and the voltage input, V <sub>DD</sub> , port. DUT includes an integrated shunt resistor for ESD protection.
V <sub>GG</sub>	15	Gate DC Input Pad connects to the voltage input port V <sub>GG</sub> .
GND	Paddle	Connects to ground.
NC	1-6, 8-14, 16-18, & 20	Not used internally. Connected to ground on test board.

### CHARACTERIZATION TEST BOARD

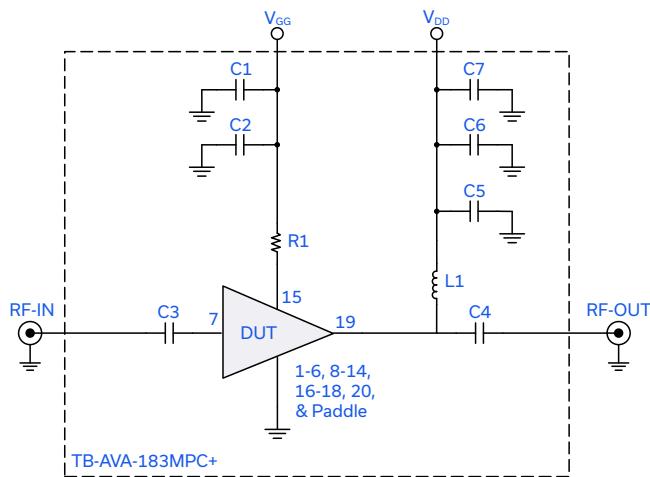


Figure 2. DUT soldered on Mini-Circuits Characterization Test Board: TB-AVA-183MPC+

Gain, Return Loss, Output Power at 1dB Compression (P1dB), Output IP3 (OIP3) and Noise Figure measured using PNA-X N5247B Microwave Network Analyzer:

**Conditions**

1. Gain and Return Loss: P<sub>IN</sub> = -25 dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.
3. V<sub>DD</sub> = +8V, I<sub>DD</sub> = 160 mA

**Caution:** Permanent damage to the device will occur if the Power ON and Power OFF Sequences are not followed.

**Power ON Sequence:**

- 1) Set V<sub>GG</sub> = -2V. Apply V<sub>GG</sub>.
- 2) Set V<sub>DD</sub> = +8V. Apply V<sub>DD</sub>.
- 3) Increase V<sub>GG</sub> to obtain desired I<sub>DD</sub> as shown in specification table.
- 4) Apply RF Signal.

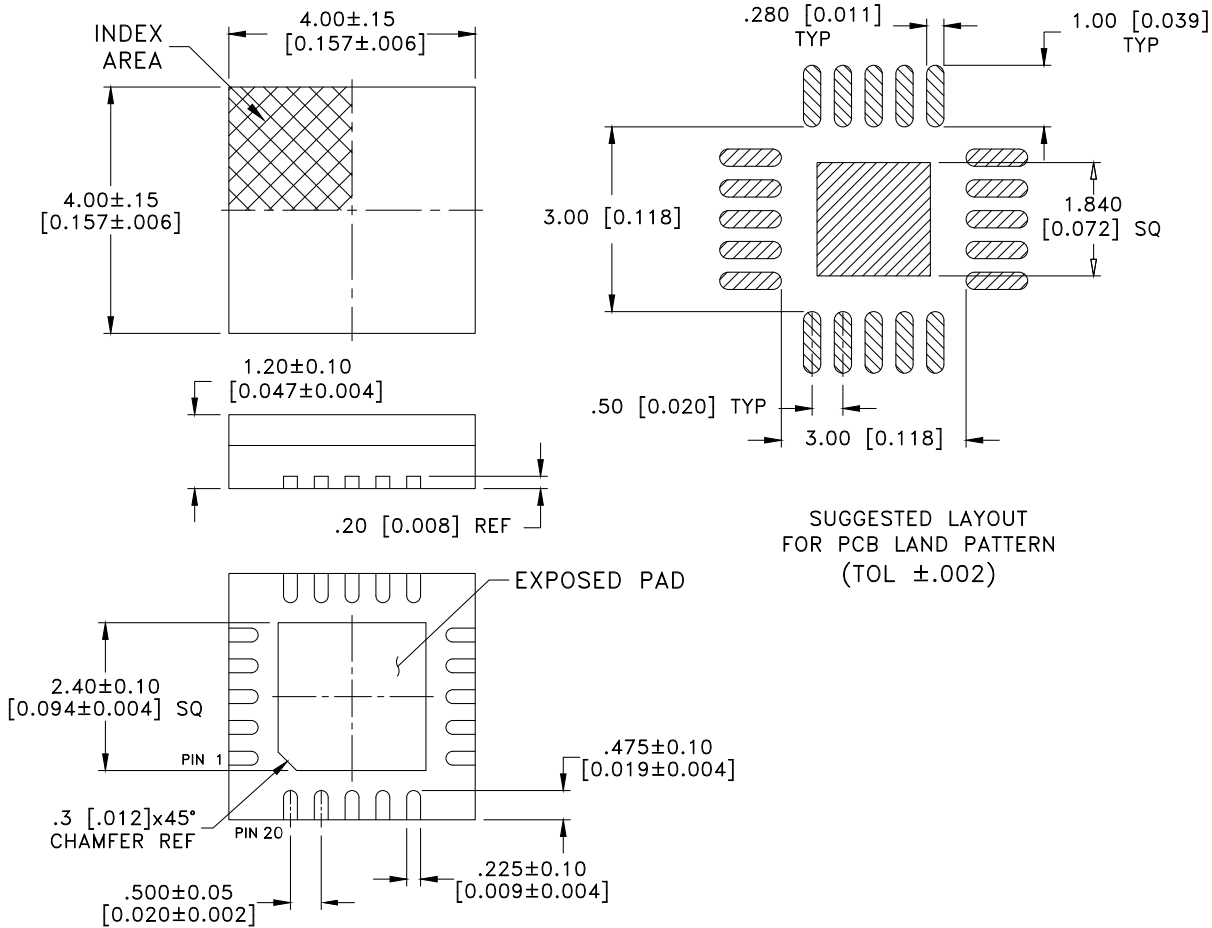
**Power OFF Sequence:**

- 1) Turn off RF Signal.
- 2) Adjust V<sub>GG</sub> down to -2V.
- 3) Turn off V<sub>DD</sub>.
- 4) Turn off V<sub>GG</sub>.

Component	Vendor	Vendor P/N	Value	Size
C1, C7	Samsung	CL31B106KBHNNNE	10μF	1206
C2, C6	AVX	06035C104KAT2A	0.1μF	0603
C5	Murata	GRM1885C1H101GA01D	100pF	0603
C3, C4	AVX	550L104KTT	0.1μF	0402
R1	KOA	RK73H1ETTP1001F	1kΩ	0402
L1	PICONICS	CC36T44K240G5-C	0.6μH	2.5mmx3.8mm



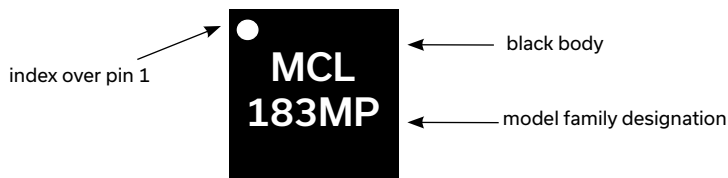
### CASE STYLE DRAWING



Weight: 0.1 grams  
Dimensions are in inches [mm].

Figure 3. DG1847-1 Case Style Drawing

### PRODUCT MARKING



Marking may contain other features or characters for internal lot control

Figure 4. AVA-183MP+ Product Marking





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ADDITIONAL DETAILED INFORMATION IS AVAILABLE ON OUR DASH BOARD

[CLICK HERE](#)

<b>Performance Data</b>	Data Graphs S-Parameter (S2P Files) Data Set (.zip file)
<b>Case Style</b>	DG1847-1. QFN-style package, exposed paddle, Lead Finish: PPF
<b>RoHs Status</b>	Compliant
<b>Tape &amp; Reel</b> Standard quantities available on reel	F66 7" reels with 20, 50, 100, 200, 500, or 1000 devices
<b>Suggested Layout for PCB Design</b>	PL-750
<b>Evaluation Board</b>	TB-AVA-183MPC+ Gerber File
<b>Environmental Ratings</b>	ENV08T10
<b>Product Handling</b>	The use of no-clean solder is recommended. This package cannot be subjected to aqueous wash.

### NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at [www.minicircuits.com/terms/viewterm.html](http://www.minicircuits.com/terms/viewterm.html)



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